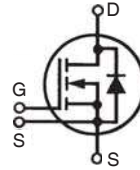


Linear Power MOSFET w/Extended FBSOA

IXTN8N150L

N-Channel Enhancement Mode
Guaranteed FBSOA

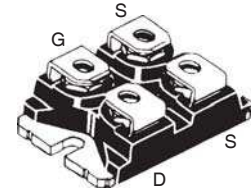


$$V_{DSS} = 1500V$$

$$I_{D25} = 7.5A$$

$$R_{DS(on)} = 3.6\Omega$$

miniBLOC, SOT-227 B
E153432



G = Gate D = Drain
S = Source S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	1500	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	1500	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$	7.5	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	20	A
P_D	$T_C = 25^\circ C$	545	W
T_J		-55 to +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 to +150	$^\circ C$
V_{ISOL}	50/60 Hz, RMS, $t = 1$ minute	2500	V~
	$I_{ISOL} \leq 1mA$, $t = 1s$	3000	V~
M_d	Mounting Torque for Base Plate	1.5/13	Nm/lb.in.
	Terminal Connection Torque	1.3/11.5	Nm/lb.in.
Weight		30	g

Features

- Designed for Linear Operations
- International Standard Package
- Molding Epoxies Meet UL94 V-0 Flammability Classification
- Guaranteed FBSOA at $60^\circ C$
- miniBLOC with Aluminum Nitride Isolation
- Low $R_{DS(on)}$ HDMOS™ Process
- Rugged Polysilicon Gate Cell Structure
- Low Package Inductance

Applications

- Programmable Loads
- Current Regulators
- DC-DC Convertors
- Battery Chargers
- DC Choppers
- Temperature and Lighting Controls

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 1mA$	1500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	5.0		8.0 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_J = 125^\circ C$			50 μA 3 mA
$R_{DS(on)}$	$V_{GS} = 20V$, $I_D = 4A$, Note 1			3.6 Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 50\text{V}$, $I_D = 4\text{A}$, Note 1	1.4	2.3	3.2 S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		8000	pF
C_{oss}			405	pF
C_{rss}			70	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 15\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 4\text{A}$ $R_G = 2\Omega$ (External)		36	ns
t_r			18	ns
$t_{d(off)}$			90	ns
t_f			95	ns
$Q_{g(on)}$	$V_{GS} = 15\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 4\text{A}$		250	nC
Q_{gs}			80	nC
Q_{gd}			116	nC
R_{thJC}		0.05		0.23°C/W
R_{thCS}				$^\circ\text{C/W}$

Safe Operating Area Specification

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 1000\text{V}$, $I_D = 0.40\text{A}$, $T_C = 60^\circ\text{C}$, $T_P = 3\text{s}$	400		W

Source-Drain Diode

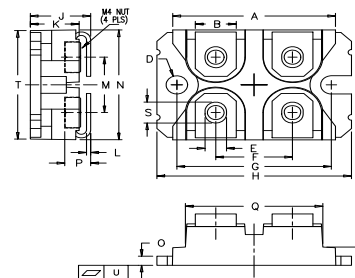
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			8 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			32 A
V_{SD}	$I_F = 8\text{A}$, $V_{GS} = 0\text{V}$, Note 1			1.2 V
t_{rr}	$I_F = I_S$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 100\text{V}$		1700	ns

Notes: 1. Pulse Test, $t \leq 300\mu\text{s}$; Duty Cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

SOT-227B (IXTN) Outline



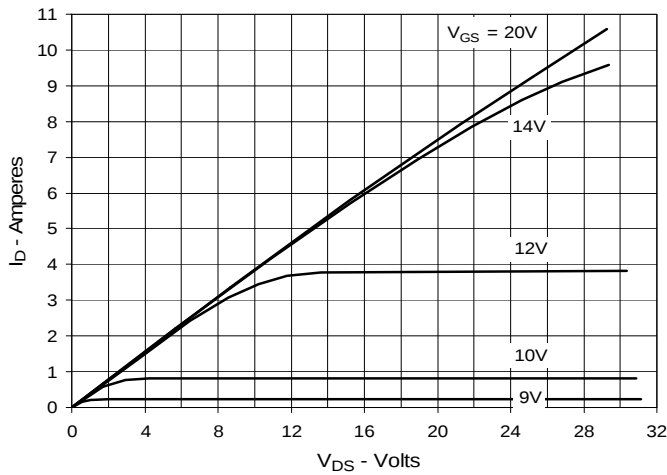
(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

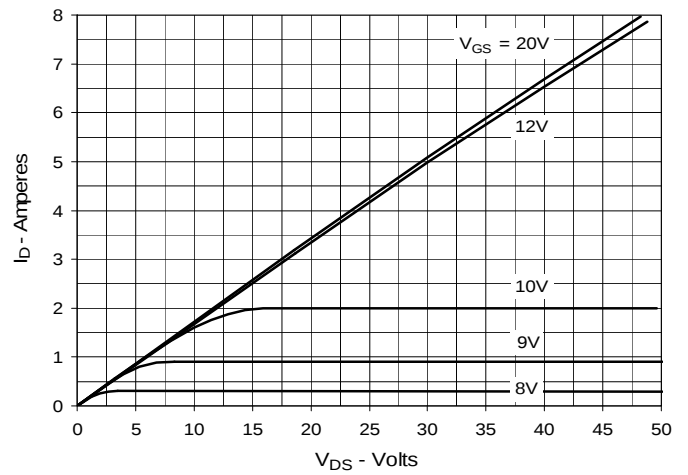
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

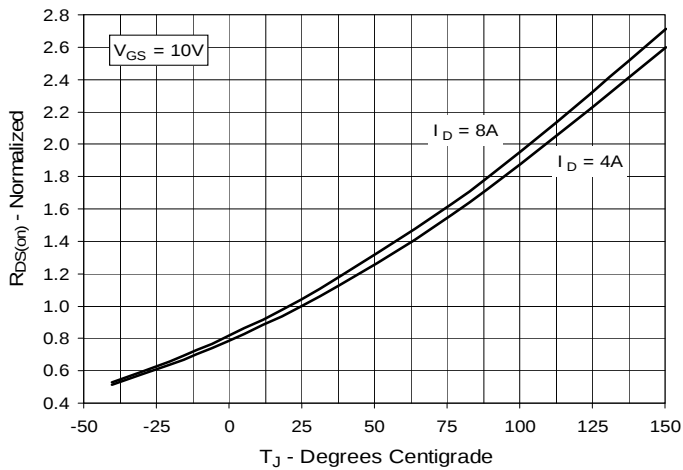
**Fig. 1. Extended Output Characteristics
@ 25°C**



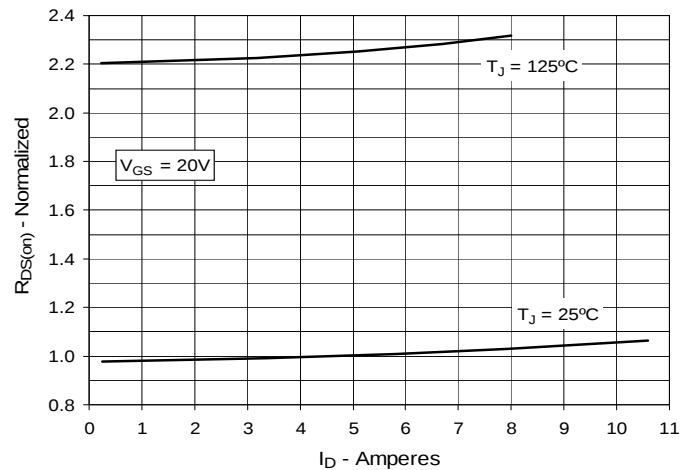
**Fig. 2. Output Characteristics
@ 125°C**



**Fig. 3. $R_{DS(on)}$ Normalized to $I_D = 4A$ Value
vs. Junction Temperature**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 4A$ Value
vs. Drain Current**



**Fig. 5. Maximum Drain Current vs.
Case Temperature**

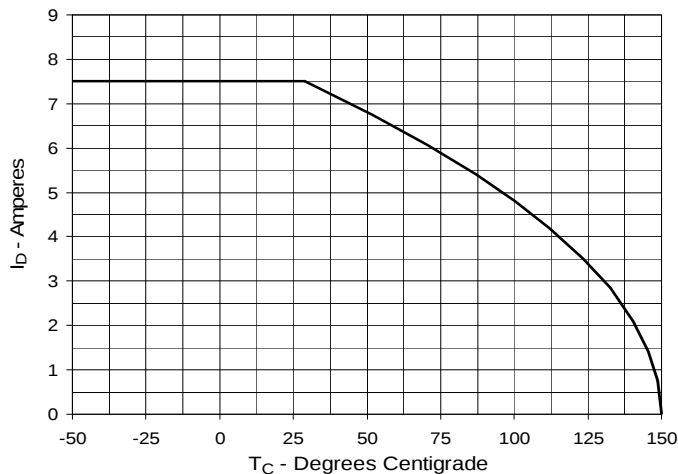


Fig. 6. Input Admittance

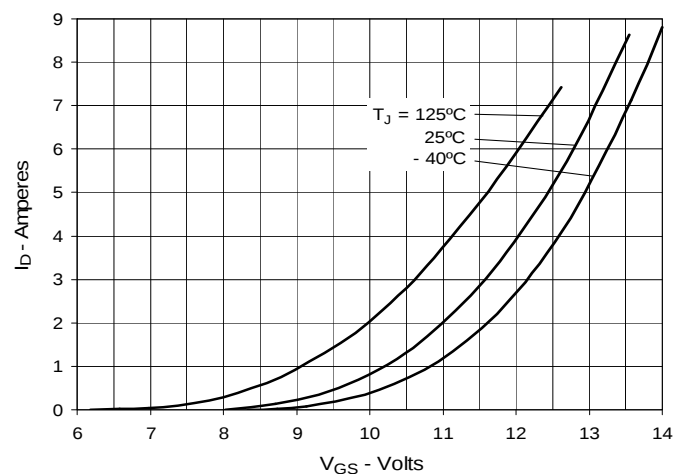


Fig. 7. Transconductance

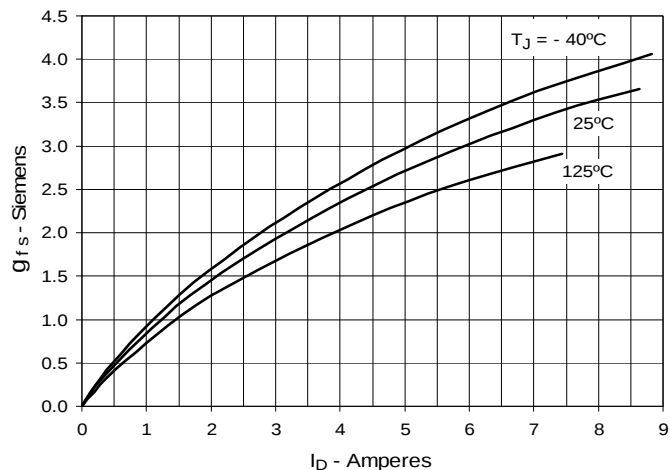


Fig. 8. Forward Voltage Drop of Intrinsic Diode

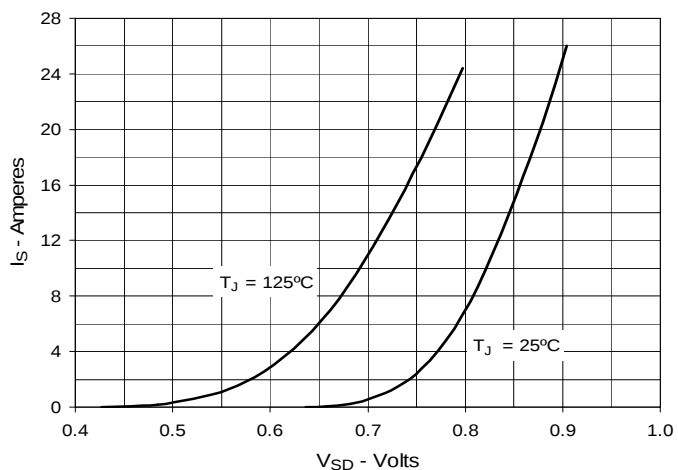


Fig. 9. Gate Charge

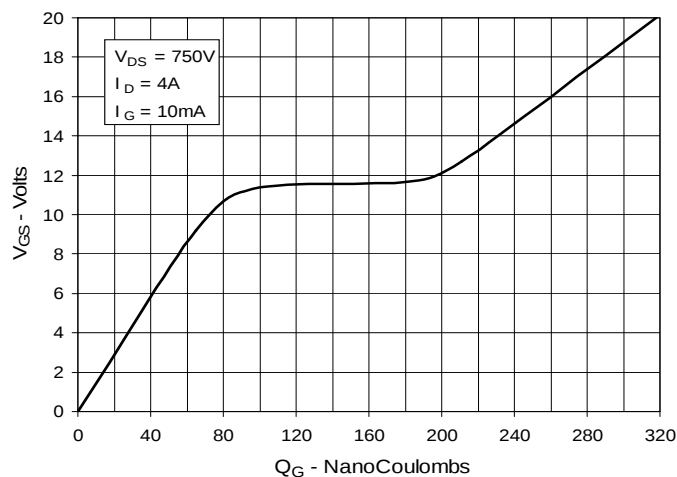


Fig. 10. Capacitance

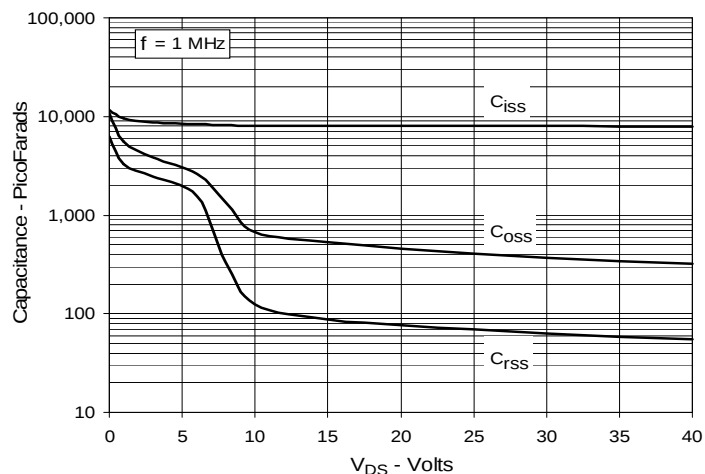


Fig. 11. Maximum Transient Thermal Impedance

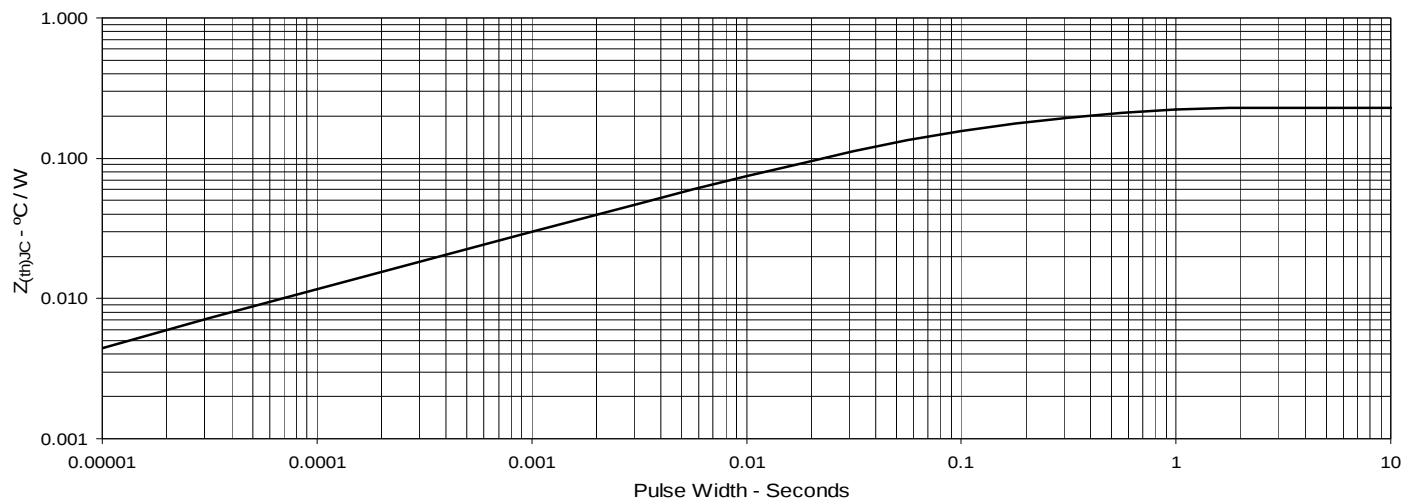


Fig. 12. Forward-Bias Safe Operating Area @
 $T_C = 25^\circ\text{C}$

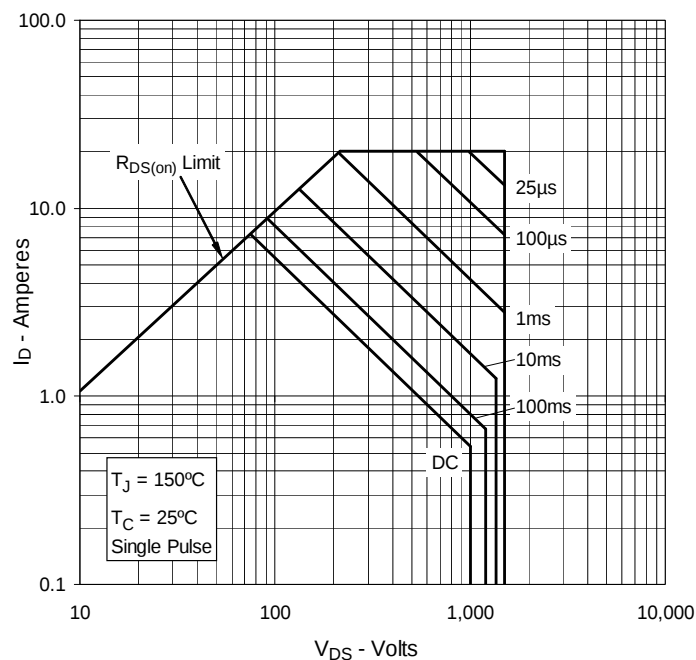


Fig. 13. Forward-Bias Safe Operating Area
@ $T_C = 60^\circ\text{C}$

